

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

PHONE: (215) 631-9840 FAX: (215) 631-9855

MS1409

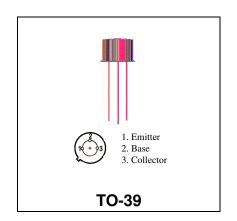
RF & MICROWAVE TRANSISTOR VHF COMMUNICATIONS

Features

- 175 MHz
- 28 VOLTS
- P_{OUT} = 2.5 W
- G_P = 10 dB MINIMUM
- COMMON EMITTER CONFIGURATION

DESCRIPTION:

The MS1409 is a NPN silicon transistor designed for high power gain VHF and UHF communication applications. Gold metalization and diffused emitter ballast resistors provide superior long term reliability.



ABSOLUTE MAXIMUM RATINGS (Tease = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base Voltage	65	V
V _{CEO}	Collector-emitter Voltage	40	V
V_{EBO}	Emitter-base Voltage	4.0	V
P _{DISS}	Total Power Dissipation	7.0	W
Ic	Collector Peak Current	1.0	A
T _J	Junction Temperature	200	oC
T _{STG}	Storage Temperature	-65 to 200	ōC

Thermal Data

R _{TH(J-CASE)}	Thermal Resistance Junction-case	25	°C/W
III(U-CASE)		_	-,

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ELECTRICAL SPECIFICATIONS (Tcase = 25^{\circ}C) STATIC

Symbol	Test Conditions		Value			
		Min.	Typ.	Max.	Unit	
BVebo	$I_E = 0.10 \text{ mA}$	$I_C = 0 \text{ mA}$	4.0			V
BVcbo	$I_C = 0.3 \text{ mA}$	I _E = 0 mA	65			V
BVceo	$I_C = 3 \text{ mA}$	I _S = 0 mA	40			V
Iceo	V _{CE} = 30 V				0.1	mA
H _{FE}	V _{CE} = 5 V	I _C = 100 mA	20		200	В

DYNAMIC

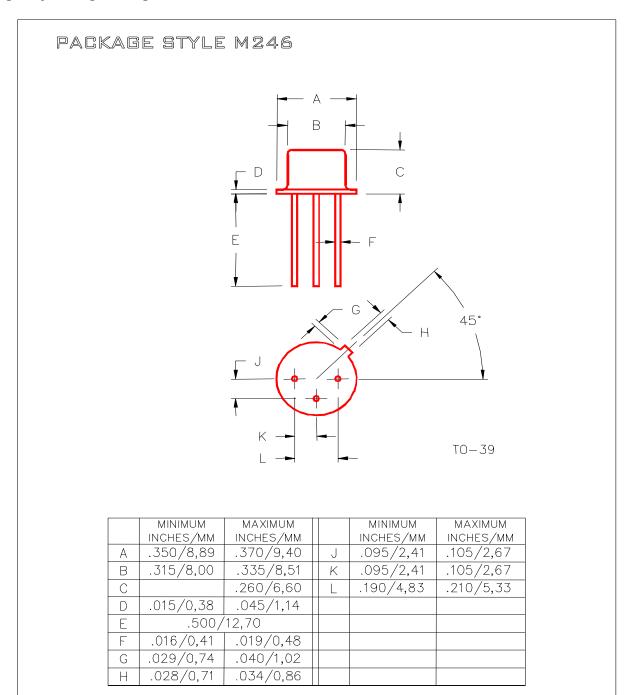
Symbol	Test Conditions			Value		Unit	
			Min.	Typ.	Max.	Ollit	
P _{OUT}	f =175 MHz	$P_{IN} = 0.25W$	$V_{CC} = 28V$	2.5			W
ης	f =175 MHz	$P_{IN} = 0.25W$	$V_{CC} = 28V$	50			%
G _P	f =175 MHz	$P_{IN} = 0.25W$	$V_{CC} = 28V$	10			dB
Сов	f =1.0MHz	V _{CB} = 30V				10	pf

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PACKAGE MECHANICAL DATA



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